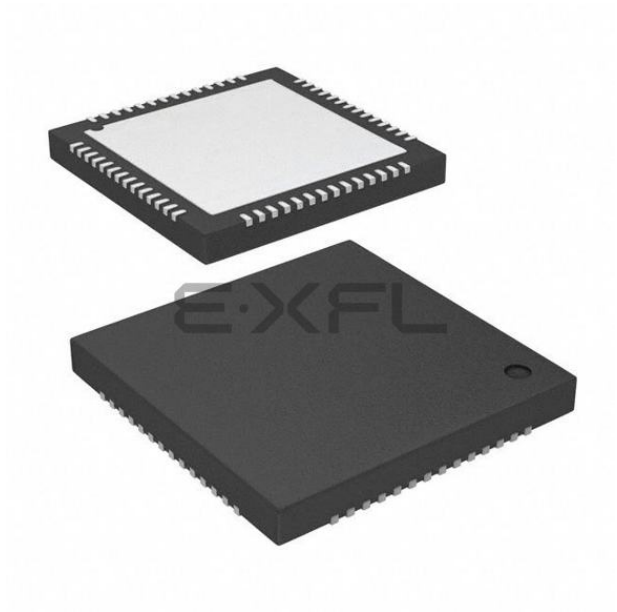


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Bluetooth, Brown-out Detect/Reset, Cap Sense, LCD, LVD, POR, PWM, SmartCard, SmartSense, WDT
Number of I/O	36
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 8x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	56-UFQFN Exposed Pad
Supplier Device Package	56-QFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4247lqi-bl483t

More Information

Cypress provides a wealth of data at http://www.cypress.com to help you to select the right PSoC device for your design, and to help you to quickly and effectively integrate the device into your design. For a comprehensive list of resources, see the introduction page for Bluetooth® Low Energy (BLE) Products. Following is an abbreviated list for PRoC BLE:

- Overview: PSoC Portfolio, PSoC Roadmap
- Product Selectors: PSoC 1, PSoC 3, PSoC 4, PRoC BLE, PSoC 4 BLE, PSoC 5LP In addition, PSoC Creator includes a device selection tool.
- Application Notes: Cypress offers a large number of PSoC application notes coverting a broad range of topics, from basic to advanced level. Recommended application notes for getting started with PRoC BLE are:
  - AN94020: Getting Started with PRoC BLE
  - AN97060: PSoC 4 BLE and PRoC BLE - Over-The-Air (OTA) Device Firmware Upgrade (DFU) Guide
  - AN91184: PSoC 4 BLE - Designing BLE Applications
  - AN91162: Creating a BLE Custom Profile
  - AN91445: Antenna Design and RF Layout Guidelines
  - AN96841: Getting Started With EZ-BLE Module
  - AN85951: PSoC 4 CapSense Design Guide
  - AN95089: PSoC 4/PRoC BLE Crystal Oscillator Selection and Tuning Techniques
  - AN92584: Designing for Low Power and Estimating Battery Life for BLE Applications
- Technical Reference Manual (TRM) is in two documents:
  - Architecture TRM details each PRoC BLE functional block
  - Registers TRM describes each of the PRoC BLE registers
- Development Kits:
  - CY8CKIT-042-BLE-A Pioneer Kit, is a flexible, Arduino-compatible, Bluetooth LE development kit for PSoC 4 BLE and PRoC BLE.
  - CY8CKIT-142, PSoC 4 BLE Module, features a PSoC 4 BLE device, two crystals for the antenna matching network, a PCB antenna and other passives, while providing access to all GPIOs of the device.
  - CY8CKIT-143, PSoC 4 BLE 256KB Module, features a PSoC 4 BLE 256KB device, two crystals for the antenna matching network, a PCB antenna and other passives, while providing access to all GPIOs of the device.
  - The MiniProg3 device provides an interface for flash programming and debug.

PSoC Creator

PSoC Creator is a free Windows-based Integrated Design Environment (IDE). It enables concurrent hardware and firmware design of PSoC 3, PSoC 4, and PSoC 5LP based systems. Create designs using classic, familiar schematic capture supported by over 100 pre-verified, production-ready PSoC Components; see the list of component datasheets. With PSoC Creator, you can:

1. Drag and drop component icons to build your hardware system design in the main design workspace
2. Codesign your application firmware with the PSoC hardware, using the PSoC Creator IDE C compiler
3. Configure components using the configuration tools
4. Explore the library of 100+ components
5. Review component datasheets

Figure 1. Multiple-Sensor Example Project in PSoC Creator Contents

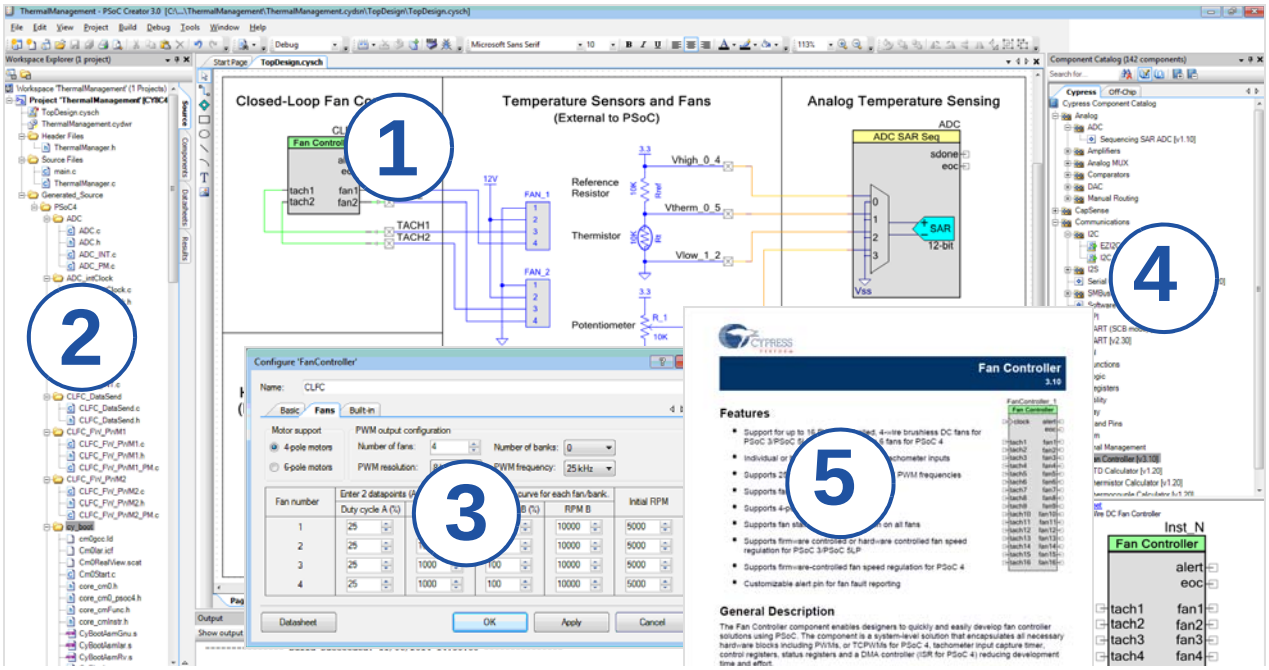
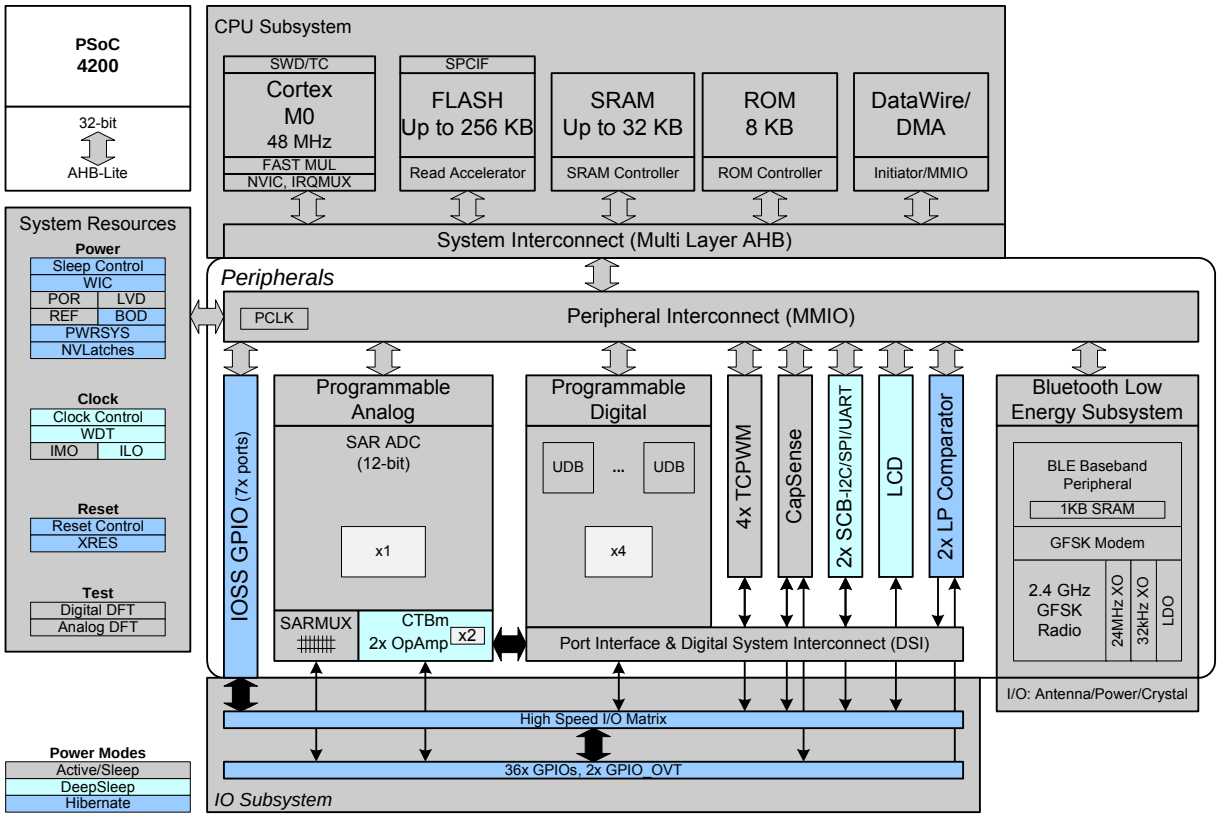


Figure 2. Block Diagram



The PSoC 4200_BL devices include extensive support for programming, testing, debugging, and tracing both hardware and firmware.

The Arm SWD interface supports all programming and debug features of the device.

Complete debug-on-chip functionality enables full-device debugging in the final system using the standard production device. It does not require special interfaces, debugging pods, simulators, or emulators. Only the standard programming connections are required to fully support debugging.

The PSoC Creator IDE provides fully integrated programming and debugging support for the PSoC 4200_BL devices. The SWD interface is fully compatible with industry-standard third-party tools. With the ability to disable debug features, very robust flash protection, and allowing customer-proprietary functionality to be implemented in on-chip programmable blocks, the PSoC 4200_BL family provides a level of security not possible with multi-chip application solutions or with microcontrollers.

Debug circuits are enabled by default and can only be disabled in firmware. If not enabled, the only way to re-enable them is to erase the entire device, clear flash protection, and reprogram the device with the new firmware that enables debugging.

Additionally, all device interfaces can be permanently disabled (device security) for applications concerned about phishing attacks due to a maliciously reprogrammed device or attempts to defeat security by starting and interrupting flash programming sequences. Because all programming, debug, and test interfaces are disabled when maximum device security is enabled, PSoC 4200_BL with device security enabled may not be returned for failure analysis. This is a trade-off the PSoC 4200_BL allows the customer to make.

Functional Definition

CPU and Memory Subsystem

CPU

The Cortex-M0 CPU in PSoC 4200_BL is part of the 32-bit MCU subsystem, which is optimized for low-power operation with extensive clock gating. It mostly uses 16-bit instructions and executes a subset of the Thumb-2 instruction set. This enables fully compatible binary upward migration of the code to higher-performance processors such as Cortex-M3 and M4. The Cypress implementation includes a hardware multiplier that provides a 32-bit result in one cycle. It includes a nested vectored interrupt controller (NVIC) block with 32 interrupt inputs and a wakeup interrupt controller (WIC). The WIC can wake the processor up from the Deep Sleep mode, allowing power to the main processor to be switched off when the chip is in the Deep Sleep mode. The Cortex-M0 CPU provides a nonmaskable interrupt (NMI) input, which is made available to the user when it is not in use for system functions requested by the user.

The CPU also includes an SWD interface, which is a 2-wire form of JTAG; the debug configuration used for PSoC 4200_BL has four break-point (address) comparators and two watchpoint (data) comparators.

Flash

The PSoC 4200_BL device has a flash module with 256 KB of flash memory, tightly coupled to the CPU to improve average access times from the flash block. The flash block is designed to deliver 2 wait-state (WS) access time at 48 MHz and with 1-WS access time at 24 MHz. The flash accelerator delivers 85% of single-cycle SRAM access performance on average. Part of the flash module can be used to emulate EEPROM operation if required. Maximum erase and program time is 20 ms per row (256 bytes). This also applies to the emulated EEPROM.

SRAM

SRAM memory is retained during Hibernate.

SROM

The 8-KB supervisory ROM contains a library of executable functions for flash programming. These functions are accessed through supervisory calls (SVC) and enable in-system programming of the flash memory.

DMA

A DMA engine, with eight channels, is provided that can do 32-bit transfers and has chainable ping-pong descriptors.

System Resources

Power System

The power system is described in detail in the section Power on page 16. It provides an assurance that the voltage levels are as required for the respective modes, and can either delay the mode entry (on power-on reset (POR), for example) until voltage levels are as required or generate resets (brownout detect (BOD)) or interrupts when the power supply reaches a particular programmable level between 1.8 and 4.5 V (low voltage detect (LVD)).

PSoC 4200_BL operates with a single external supply (1.71 to 5.5 V without radio, and 1.9 V to 5.5 V with radio). The device has five different power modes; transitions between these modes are managed by the power system. PSoC 4200_BL provides Sleep, Deep Sleep, Hibernate, and Stop low-power modes. Refer to the *Technical Reference Manual* for more details.

Clock System

The PSoC 4200_BL clock system is responsible for providing clocks to all subsystems that require clocks and for switching between different clock sources without glitching. In addition, the clock system ensures that no metastable conditions occur.

The clock system for PSoC 4200_BL consists of the internal main oscillator (IMO), the internal low-speed oscillator (ILO), the 24-MHz external crystal oscillator (ECO) and the 32-kHz watch crystal oscillator (WCO). In addition, an external clock may be supplied from a pin.

IMO Clock Source

The IMO is the primary source of internal clocking in PSoC 4200_BL. It is trimmed during testing to achieve the specified accuracy. Trim values are stored in nonvolatile latches (NVL). Additional trim settings from flash can be used to compensate for changes. The IMO default frequency is 24 MHz and it can be adjusted between 3 to 48 MHz in steps of 1 MHz. The IMO tolerance with Cypress-provided calibration settings is ±2%.

ILO Clock Source

The ILO is a very low-power oscillator, which is primarily used to generate clocks for the peripheral operation in the Deep Sleep mode. ILO-driven counters can be calibrated to the IMO to improve accuracy. Cypress provides a software component, which does the calibration.

External Crystal Oscillator (ECO)

The ECO is used as the active clock for the BLE subsystem to meet the ±50-ppm clock accuracy of the Bluetooth 4.2 Specification. PSoC 4200_BL includes a tunable load capacitor to tune the crystal clock frequency by measuring the actual clock frequency. The high-accuracy ECO clock can also be used as a system clock.

Watch Crystal Oscillator (WCO)

The WCO is used as the sleep clock for the BLE subsystem to meet the ±500-ppm clock accuracy for the Bluetooth 4.2 Specification. The sleep clock provides an accurate sleep timing and enables wakeup at the specified advertisement and connection intervals. The WCO output can be used to realize the real-time clock (RTC) function in firmware.

Watchdog Timer

A watchdog timer is implemented in the clock block running from the ILO or from the WCO; this allows the watchdog operation during Deep Sleep and generates a watchdog reset if not serviced before the timeout occurs. The watchdog reset is recorded in the Reset Cause register. With the WCO and firmware, an accurate real-time clock (within the bounds of the 32-kHz crystal accuracy) can be realized.

Analog Blocks

12-bit SAR ADC

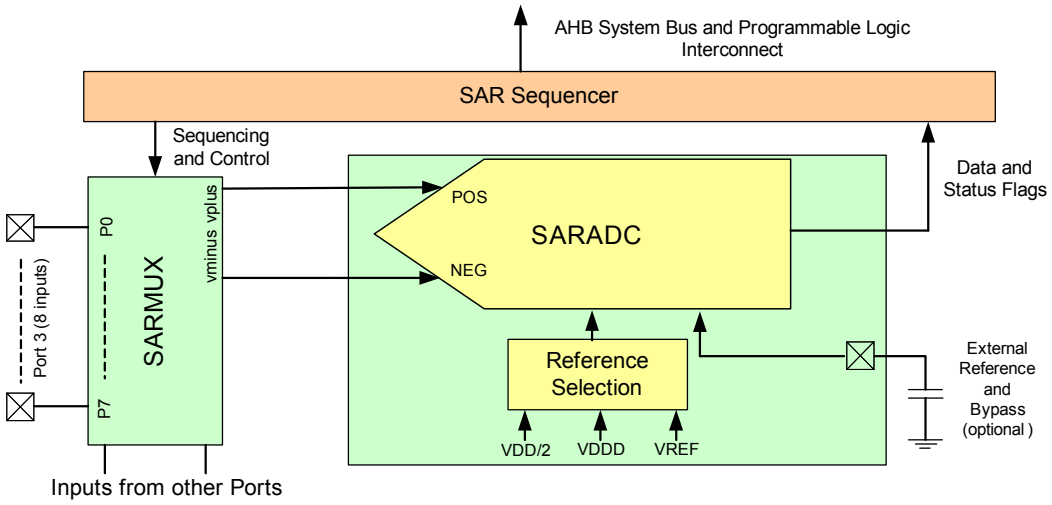
The 12-bit, 1-Msps SAR ADC can operate at a maximum clock rate of 18 MHz and requires a minimum of 18 clocks at that frequency to do a 12-bit conversion.

The block functionality is augmented for the user by adding a reference buffer to it (trimmable to ±1%) and by providing the choice of three internal voltage references, V_{DD}, $V_{DD}/2$, and V_{REF} (nominally 1.024 V), as well as an external reference through a GPIO pin. The Sample-and-Hold (S/H) aperture is programmable; it allows the gain bandwidth requirements of the amplifier driving the SAR inputs, which determine its settling time, to be relaxed if required. System performance will be 65 dB for true 12-bit precision provided appropriate references are used and system noise levels permit it. To improve the performance in noisy conditions, it is possible to provide an external bypass (through a fixed pin location) for the internal reference amplifier.

The SAR is connected to a fixed set of pins through an 8-input sequencer. The sequencer cycles through the selected channels autonomously (sequencer scan) and does so with zero switching overhead (that is, the aggregate sampling bandwidth is equal to 1 Msps whether it is for a single channel or distributed over several channels). The sequencer switching is effected through a state machine or through firmware-driven switching. A feature provided by the sequencer is the buffering of each channel to reduce CPU interrupt-service requirements. To accommodate signals with varying source impedances and frequencies, it is possible to have different sample times programmable for each channel. Also, the signal range specification through a pair of range registers (low and high range values) is implemented with a corresponding out-of-range interrupt if the digitized value exceeds the programmed range; this allows fast detection of out-of-range values without having to wait for a sequencer scan to be completed and the CPU to read the values and check for out-of-range values in software.

The SAR is able to digitize the output of the on-chip temperature sensor for calibration and other temperature-dependent functions. The SAR is not available in Deep Sleep and Hibernate modes as it requires a high-speed clock (up to 18 MHz). The SAR operating range is 1.71 to 5.5 V.

Figure 4. SAR ADC System Diagram



Opamps (CTBm Block)

PSoC 42X8_BLE has four opamps with Comparator modes, which allow most common analog functions to be performed on-chip, eliminating external components. PGAs, voltage buffers, filters, transimpedance amplifiers, and other functions can be realized with external passives saving power, cost, and space. The on-chip opamps are designed with enough bandwidth to drive the sample-and-hold circuit of the ADC without requiring external buffering.

Temperature Sensor

PSoC 4200_BL has an on-chip temperature sensor. This consists of a diode, which is biased by a current source that can be disabled to save power. The temperature sensor is connected to the ADC, which digitizes the reading and produces a temperature value by using a Cypress-supplied software that includes calibration and linearization.

Low-Power Comparators

PSoC 4200_BL has a pair of low-power comparators, which can also operate in Deep Sleep and Hibernate modes. This allows the analog system blocks to be disabled while retaining the ability to monitor external voltage levels during low-power modes. The comparator outputs are normally synchronized to avoid metastability unless operating in an asynchronous power mode (Hibernate) where the system wake-up circuit is activated by a comparator-switch event.

Pinouts

Table 1 shows the pin list for the PSoC 4200_BL device. Port 3 consists of the high-speed analog inputs for the SAR mux. All pins support CSD CapSense and analog mux bus connections.

Table 1. PSoC 4200_BL Pin List (QFN Package)

Pin	Name	Type	Description
1	VDDD	POWER	1.71-V to 5.5-V digital supply
2	XTAL32O/P6.0	CLOCK	32.768-kHz crystal
3	XTAL32I/P6.1	CLOCK	32.768-kHz crystal or external clock input
4	XRES	RESET	Reset, active LOW
5	P4.0	GPIO	Port 4 Pin 0, lcd, csd
6	P4.1	GPIO	Port 4 Pin 1, lcd, csd
7	P5.0	GPIO	Port 5 Pin 0, lcd, csd
8	P5.1	GPIO	Port 5 Pin 1, lcd, csd
9	VSSD	GROUND	Digital ground
10	VDDR	POWER	1.9-V to 5.5-V radio supply
11	GANT1	GROUND	Antenna shielding ground
12	ANT	ANTENNA	Antenna pin
13	GANT2	GROUND	Antenna shielding ground
14	VDDR	POWER	1.9-V to 5.5-V radio supply
15	VDDR	POWER	1.9-V to 5.5-V radio supply
16	XTAL24I	CLOCK	24-MHz crystal or external clock input
17	XTAL24O	CLOCK	24-MHz crystal
18	VDDR	POWER	1.9-V to 5.5-V radio supply
19	P0.0	GPIO	Port 0 Pin 0, lcd, csd
20	P0.1	GPIO	Port 0 Pin 1, lcd, csd
21	P0.2	GPIO	Port 0 Pin 2, lcd, csd
22	P0.3	GPIO	Port 0 Pin 3, lcd, csd
23	VDDD	POWER	1.71-V to 5.5-V digital supply
24	P0.4	GPIO	Port 0 Pin 4, lcd, csd
25	P0.5	GPIO	Port 0 Pin 5, lcd, csd
26	P0.6	GPIO	Port 0 Pin 6, lcd, csd
27	P0.7	GPIO	Port 0 Pin 7, lcd, csd
28	P1.0	GPIO	Port 1 Pin 0, lcd, csd
29	P1.1	GPIO	Port 1 Pin 1, lcd, csd
30	P1.2	GPIO	Port 1 Pin 2, lcd, csd
31	P1.3	GPIO	Port 1 Pin 3, lcd, csd
32	P1.4	GPIO	Port 1 Pin 4, lcd, csd
33	P1.5	GPIO	Port 1 Pin 5, lcd, csd
34	P1.6	GPIO	Port 1 Pin 6, lcd, csd
35	P1.7	GPIO	Port 1 Pin 7, lcd, csd
36	VDDA	POWER	1.71-V to 5.5-V analog supply
37	P2.0	GPIO	Port 2 Pin 0, lcd, csd
38	P2.1	GPIO	Port 2 Pin 1, lcd, csd
39	P2.2	GPIO	Port 2 Pin 2, lcd, csd

Electrical Specifications

Absolute Maximum Ratings

Table 5. Absolute Maximum Ratings[1]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID1	V_{DDD_ABS}	Analog, digital, or radio supply relative to V_{SS} (V_{SSD} = V_{SSA})	–0.5	–	6	V	Absolute max
SID2	V_{CCD_ABS}	Direct digital core voltage input relative to V_{SSD}	–0.5	–	1.95	V	Absolute max
SID3	V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DD} +0.5	V	Absolute max
SID4	I_{GPIO_ABS}	Maximum current per GPIO	–25	–	25	mA	Absolute max
SID5	$I_{GPIO\_injection}$	GPIO injection current, Max for V_{IH} > V_{DDD}, and Min for V_{IL} < V_{SS}	–0.5	–	0.5	mA	Absolute max, current injected per pin
BID57	ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	–
BID58	ESD_CDM	Electrostatic discharge charged device model	500	–	–	V	–
BID61	LU	Pin current for latch-up	–200	–	200	mA	–

Device-Level Specifications

All specifications are valid for –40 °C ≤ TA ≤ 85 °C and TJ ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 6. DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID6	V_{DD}	Power supply input voltage (V_{DDA} = V_{DDD} = V_{DD})	1.8	–	5.5	V	With regulator enabled
SID7	V_{DD}	Power supply input voltage unregulated (V_{DDA} = V_{DDD} = V_{DD})	1.71	1.8	1.89	V	Internally unregulated Supply
SID8	V_{DDR}	Radio supply voltage (Radio ON)	1.9	–	5.5	V	–
SID8A	V_{DDR}	Radio supply voltage (Radio OFF)	1.71	–	5.5	V	–
SID9	V_{CCD}	Digital regulator output voltage (for core logic)	–	1.8	–	V	–
SID10	C_{VCCD}	Digital regulator output bypass capacitor	1	1.3	1.6	µF	X5R ceramic or better
Active Mode, V_{DD} = 1.71 V to 5.5 V							–
SID13	I_{DD3}	Execute from flash; CPU at 3 MHz	–	2.1	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID14	I_{DD4}	Execute from flash; CPU at 3 MHz	–	–	–	mA	T = –40 C to 85 °C
SID15	I_{DD5}	Execute from flash; CPU at 6 MHz	–	2.5	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID16	I_{DD6}	Execute from flash; CPU at 6 MHz	–	–	–	mA	T = –40 °C to 85 °C
SID17	I_{DD7}	Execute from flash; CPU at 12 MHz	–	4	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID18	I_{DD8}	Execute from flash; CPU at 12 MHz	–	–	–	mA	T = –40 °C to 85 °C

Note
1. Usage above the absolute maximum conditions listed in Table 5 may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.

Table 6. DC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID19	I_{DD9}	Execute from flash; CPU at 24 MHz	–	7.1	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID20	I_{DD10}	Execute from flash; CPU at 24 MHz	–	–	–	mA	T = –40 °C to 85 °C
SID21	I_{DD11}	Execute from flash; CPU at 48 MHz	–	13.4	–	mA	T = 25 °C, V_{DD} = 3.3 V
SID22	I_{DD12}	Execute from flash; CPU at 48 MHz	–	–	–	mA	T = –40 °C to 85 °C
Sleep Mode, V_{DD} = 1.8 to 5.5 V							
SID23	I_{DD13}	IMO on	–	–	–	mA	T = 25 °C, VDD = 3.3 V, SYSCLK = 3 MHz
Sleep Mode, V_{DD} and V_{DDR} = 1.9 to 5.5 V							
SID24	I_{DD14}	ECO on	–	–	–	mA	T = 25 °C, VDD = 3.3 V, SYSCLK = 3 MHz
Deep Sleep Mode, V_{DD} = 1.8 to 3.6 V							
SID25	I_{DD15}	WDT with WCO on	–	1.5	–	µA	T = 25 °C, V_{DD} = 3.3 V
SID26	I_{DD16}	WDT with WCO on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 3.6 to 5.5 V							
SID27	I_{DD17}	WDT with WCO on	–	–	–	µA	T = 25 °C, V_{DD} = 5 V
SID28	I_{DD18}	WDT with WCO on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID29	I_{DD19}	WDT with WCO on	–	–	–	µA	T = 25 °C
SID30	I_{DD20}	WDT with WCO on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 1.8 to 3.6 V							
SID31	I_{DD21}	Opamp on	–	–	–	µA	T = 25 °C, V_{DD} = 3.3 V
SID32	I_{DD22}	Opamp on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 3.6 to 5.5 V							
SID33	I_{DD23}	Opamp on	–	–	–	µA	T = 25 °C, V_{DD} = 5 V
SID34	I_{DD24}	Opamp on	–	–	–	µA	T = –40 °C to 85 °C
Deep Sleep Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID35	I_{DD25}	Opamp on	–	–	–	µA	T = 25 °C
SID36	I_{DD26}	Opamp on	–	–	–	µA	T = –40 °C to 85 °C
Hibernate Mode, V_{DD} = 1.8 to 3.6 V							
SID37	I_{DD27}	GPIO and reset active	–	150	–	nA	T = 25 °C, V_{DD} = 3.3V
SID38	I_{DD28}	GPIO and reset active	–	–	–	nA	T = –40 °C to 85 °C
Hibernate Mode, V_{DD} = 3.6 to 5.5 V							
SID39	I_{DD29}	GPIO and reset active	–	–	–	nA	T = 25 °C, V_{DD} = 5 V
SID40	I_{DD30}	GPIO and reset active	–	–	–	nA	T = –40 °C to 85 °C
Hibernate Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							

Table 6. DC Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID41	I_{DD31}	GPIO and reset active	–	–	–	nA	T = 25 °C
SID42	I_{DD32}	GPIO and reset active	–	–	–	nA	T = –40 °C to 85 °C
Stop Mode, V_{DD} = 1.8 to 3.6 V							
SID43	I_{DD33}	Stop mode current (V_{DD})	–	20	–	nA	T = 25 °C, V_{DD} = 3.3 V
SID44	I_{DD34}	Stop mode current (V_{DDR})	–	40	–-	nA	T = 25 °C, V_{DDR} = 3.3 V
SID45	I_{DD35}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C
SID46	I_{DD36}	Stop mode current (V_{DDR})	–	–	–	nA	T = –40 °C to 85 °C, V_{DDR} = 1.9 V to 3.6 V
Stop Mode, V_{DD} = 3.6 to 5.5 V							
SID47	I_{DD37}	Stop mode current (V_{DD})	–	–	–	nA	T = 25 °C, V_{DD} = 5 V
SID48	I_{DD38}	Stop mode current (V_{DDR})	–	–	–	nA	T = 25 °C, V_{DDR} = 5 V
SID49	I_{DD39}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C
SID50	I_{DD40}	Stop mode current (V_{DDR})	–	–	–	nA	T = –40 °C to 85 °C
Stop Mode, V_{DD} = 1.71 to 1.89 V (Regulator Bypassed)							
SID51	I_{DD41}	Stop mode current (V_{DD})	–	–	–	nA	T = 25 °C
SID52	I_{DD42}	Stop mode current (V_{DD})	–	–	–	nA	T = –40 °C to 85 °C

Table 7. AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID53	F_{CPU}	CPU frequency	DC	–	48	MHz	1.71 V ≤ V_{DD} ≤ 5.5 V
SID54	T_{SLEEP}	Wakeup from Sleep mode	–	0	–	µs	Guaranteed by characterization
SID55	$T_{DEEPSLEEP}$	Wakeup from Deep Sleep mode	–	–	25	µs	24-MHz IMO. Guaranteed by characterization.
SID56	$T_{HIBERNATE}$	Wakeup from Hibernate mode	–	–	0.7	ms	Guaranteed by characterization
SID57	T_{STOP}	Wakeup from Stop mode	–	–	2.2	ms	Guaranteed by characterization

Table 13. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID93	$T_{RESETWIDTH}$	Reset pulse width	1	–	–	µs	–

Analog Peripherals

Opamp

Table 14. Opamp Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
I_{DD} (Opamp Block Current. V_{DD} = 1.8 V. No Load)							
SID94	I_{DD_HI}	Power = high	–	1000	1850	µA	–
SID95	I_{DD_MED}	Power = medium	–	500	950	µA	–
SID96	I_{DD_LOW}	Power = low	–	250	350	µA	–
GBW (Load = 20 pF, 0.1 mA. V_{DDA} = 2.7 V)							
SID97	GBW_HI	Power = high	6	–	–	MHz	–
SID98	GBW_MED	Power = medium	4	–	–	MHz	–
SID99	GBW_LO	Power = low	–	1	–	MHz	–
I_{OUT_MAX} (V_{DDA} ≥ 2.7 V, 500 mV From Rail)							
SID100	$I_{OUT\_MAX\_HI}$	Power = high	10	–	–	mA	–
SID101	$I_{OUT\_MAX\_MID}$	Power = medium	10	–	–	mA	–
SID102	$I_{OUT\_MAX\_LO}$	Power = low	–	5	–	mA	–
I_{OUT} (V_{DDA} = 1.71 V, 500 mV From Rail)							
SID103	$I_{OUT\_MAX\_HI}$	Power = high	4	–	–	mA	–
SID104	$I_{OUT\_MAX\_MID}$	Power = medium	4	–	–	mA	–
SID105	$I_{OUT\_MAX\_LO}$	Power = low	–	2	–	mA	–
SID106	V_{IN}	Charge pump on, V_{DDA} ≥ 2.7 V	–0.05	–	V_{DDA} – 0.2	V	–
SID107	V_{CM}	Charge pump on, V_{DDA} ≥ 2.7 V	–0.05	–	V_{DDA} – 0.2	V	–
V_{OUT} (V_{DDA} ≥ 2.7 V)							
SID108	V_{OUT_1}	Power = high, I_{LOAD}=10 mA	0.5	–	V_{DDA} – 0.5	V	–
SID109	V_{OUT_2}	Power = high, I_{LOAD}=1 mA	0.2	–	V_{DDA} – 0.2	V	–
SID110	V_{OUT_3}	Power = medium, I_{LOAD}=1 mA	0.2	–	V_{DDA} – 0.2	V	–
SID111	V_{OUT_4}	Power = low, I_{LOAD}=0.1 mA	0.2	–	V_{DDA} – 0.2	V	–
SID112	V_{OS_TR}	Offset voltage, trimmed	1	±0.5	1	mV	High mode
SID113	V_{OS_TR}	Offset voltage, trimmed	–	±1	–	mV	Medium mode
SID114	V_{OS_TR}	Offset voltage, trimmed	–	±2	–	mV	Low mode
SID115	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–10	±3	10	µV/C	High mode
SID116	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–	µV/C	Medium mode
SID117	$V_{OS\_DR\_TR}$	Offset voltage drift, trimmed	–	±10	–	µV/C	Low mode
SID118	CMRR	DC	70	80	–	dB	V_{DDD} = 3.6-V
SID119	PSRR	At 1 kHz, 100-mV ripple	70	85	–	dB	V_{DDD} = 3.6-V
Noise							
SID120	V_{N1}	Input referred, 1 Hz–1 GHz, power = high	–	94	–	µVrms	–
SID121	V_{N2}	Input referred, 1-kHz, power = high	–	72	–	nV/rtHz	–

Table 14. Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID122	V_{N3}	Input referred, 10-kHz, power = high	–	28	–	nV/rtHz	–
SID123	V_{N4}	Input referred, 100-kHz, power = high	–	15	–	nV/rtHz	–
SID124	C_{LOAD}	Stable up to maximum load. Performance specs at 50 pF	–	–	125	pF	–
SID125	Slew_rate	Cload = 50 pF, Power = High, $V_{DDA} \geq 2.7$ V	6	–	–	V/µsec	–
SID126	T_op_wake	From disable to enable, no external RC dominating	–	300	–	µsec	–
Comp_mode (Comparator Mode; 50-mV Drive, $T_{RISE} = T_{FALL}$ (Approx.)							
SID127	T_{PD1}	Response time; power = high	–	150	–	nsec	–
SID128	T_{PD2}	Response time; power = medium	–	400	–	nsec	–
SID129	T_{PD3}	Response time; power = low	–	2000	–	nsec	–
SID130	Vhyst_op	Hysteresis	–	10	–	mV	–
Deep Sleep (Deep Sleep mode operation is only guaranteed for $V_{DDA} > 2.5$ V)							
SID131	GBW_DS	Gain bandwidth product	–	50	–	kHz	–
SID132	IDD_DS	Current	–	15	–	µA	–
SID133	Vos_DS	Offset voltage	–	5	–	mV	–
SID134	Vos_dr_DS	Offset voltage drift	–	20	–	µV/°C	–
SID135	Vout_DS	Output voltage	0.2	–	V_{DD}–0.2	V	–
SID136	Vcm_DS	Common mode voltage	0.2	–	V_{DD}–1.8	V	–

Table 15. Comparator DC Specifications[3]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID140	$V_{OFFSET1}$	Input offset voltage, Factory trim	–	–	±10	mV	–
SID141	$V_{OFFSET2}$	Input offset voltage, Custom trim	–	–	±6	mV	–
SID141A	$V_{OFFSET3}$	Input offset voltage, ultra-low-power mode	–	±12	–	mV	$V_{DDD} \geq 2.6$ V for Temp < 0°C, $V_{DDD} \geq 1.8$ V for Temp > 0 °C
SID142	V_{HYST}	Hysteresis when enabled. Common Mode voltage range from 0 to VDD –1	–	10	35	mV	–
SID143	V_{ICM1}	Input common mode voltage in normal mode	0	–	V_{DDD} –0.1	V	Modes 1 and 2
SID144	V_{ICM2}	Input common mode voltage in low power mode	0	–	V_{DDD}	V	–
SID145	V_{ICM3}	Input common mode voltage in ultra low power mode	0	–	V_{DDD} –1.15	V	$V_{DDD} \geq 2.6$ V for Temp < 0°C, $V_{DDD} \geq 1.8$ V for Temp > 0 °C
SID146	CMRR	Common mode rejection ratio	50	–	–	dB	$V_{DDD} \geq 2.7$ V
SID147	CMRR	Common mode rejection ratio	42	–	–	dB	$V_{DDD} \leq 2.7$ V
SID148	I_{CMP1}	Block current, normal mode	–	–	400	µA	–
SID149	I_{CMP2}	Block current, low power mode	–	–	100	µA	–

Note
3. ULP LCOMP operating conditions:
   - V_{DDD} 2.6 V-5.5 V for datasheet temp range < 0 °C
   - V_{DDD} 1.8 V-5.5 V for datasheet temp range ≥ 0 °C

Table 26. PWM AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID214	$T_{PWMFREQ}$	Operating frequency	F_{CLK}	–	48	MHz	–
SID215	$T_{PWMPWINT}$	Pulse width (internal)	2 × T_{CLK}	–	–	ns	–
SID216	T_{PWMEXT}	Pulse width (external)	2 × T_{CLK}	–	–	ns	–
SID217	$T_{PWMKILLINT}$	Kill pulse width (internal)	2 × T_{CLK}	–	–	ns	–
SID218	$T_{PWMKILLEXT}$	Kill pulse width (external)	2 × T_{CLK}	–	–	ns	–
SID219	$T_{PWMEINT}$	Enable pulse width (internal)	2 × T_{CLK}	–	–	ns	–
SID220	$T_{PWMENEXT}$	Enable pulse width (external)	2 × T_{CLK}	–	–	ns	–
SID221	$T_{PWMRESWINT}$	Reset pulse width (internal)	2 × T_{CLK}	–	–	ns	–
SID222	$T_{PWMRESWEXT}$	Reset pulse width (external)	2 × T_{CLK}	–	–	ns	–

I^2C

Table 27. Fixed I^2C DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID223	I_{I2C1}	Block current consumption at 100 kHz	–	–	50	µA	–
SID224	I_{I2C2}	Block current consumption at 400 kHz	–	–	155	µA	–
SID225	I_{I2C3}	Block current consumption at 1 Mbps	–	–	390	µA	–
SID226	I_{I2C4}	I^2C enabled in Deep Sleep mode	–	–	1.4	µA	–

Table 28. Fixed I^2C AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID227	F_{I2C1}	Bit rate	–	–	1	Mbps	–

LCD Direct Drive

Table 29. LCD Direct Drive DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID228	I_{LCDLOW}	Operating current in low-power mode	–	17.5	–	µA	16 × 4 small segment display at 50 Hz
SID229	C_{LCDCAP}	LCD capacitance per segment/common driver	–	500	5000	pF	–
SID230	LCD_{OFFSET}	Long-term segment offset	–	20	–	mV	–
SID231	I_{LCDOP1}	LCD system operating current V_{BIAS} = 5 V.	–	2	–	mA	32 × 4 segments. 50 Hz at 25 °C
SID232	I_{LCDOP2}	LCD system operating current. V_{BIAS} = 3.3 V	–	2	–	mA	32 × 4 segments 50 Hz at 25 °C

Table 30. LCD Direct Drive AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID233	F_{LCD}	LCD frame rate	10	50	150	Hz	–

Table 31. Fixed UART DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID234	I_{UART1}	Block current consumption at 100 kbps	–	–	55	µA	–
SID235	I_{UART2}	Block current consumption at 1000 kbps	–	–	360	µA	–

Table 32. Fixed UART AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID236	F_{UART}	Bit rate	–	–	1	Mbps	–

SPI Specifications

Table 33. Fixed SPI DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID237	I_{SPI1}	Block current consumption at 1 Mbps	–	–	360	µA	–
SID238	I_{SPI2}	Block current consumption at 4 Mbps	–	–	560	µA	–
SID239	I_{SPI3}	Block current consumption at 8 Mbps	–	–	600	µA	–

Table 34. Fixed SPI AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID240	F_{SPI}	SPI operating frequency (master; 6X oversampling)	–	–	8	MHz	–

Table 35. Fixed SPI Master Mode AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID241	T_{DMO}	MOSI valid after Sclock driving edge	–	–	18	ns	–
SID242	T_{DSI}	MISO valid before Sclock capturing edge. Full clock, late MISO sampling used	20	–	–	ns	Full clock, late MISO sampling
SID243	T_{HMO}	Previous MOSI data hold time	0	–	–	ns	Referred to Slave capturing edge

Table 36. Fixed SPI Slave Mode AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID244	T_{DMI}	MOSI valid before Sclock capturing edge	40	–	–	ns	–
SID245	T_{DSO}	MISO valid after Sclock driving edge	–	–	$42 + 3 \times T_{CPU}$	ns	–
SID246	T_{DSO_ext}	MISO valid after Sclock driving edge in external clock mode	–	–	53	ns	$V_{DD} < 3.0$ V
SID247	T_{HSO}	Previous MISO data hold time	0	–	–	ns	–
SID248	$T_{SSELSCK}$	SSEL valid to first SCK valid edge	100	–	–	ns	–

Memory

Table 37. Flash DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID249	V_{PE}	Erase and program voltage	1.71	–	5.5	V	–
SID309	T_{WS48}	Number of Wait states at 32–48 MHz	2	–	–		CPU execution from flash
SID310	T_{WS32}	Number of Wait states at 16–32 MHz	1	–	–		CPU execution from flash
SID311	T_{WS16}	Number of Wait states for 0–16 MHz	0	–	–		CPU execution from flash

Table 47. IMO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID296	$F_{IMOTOL3}$	Frequency variation from 3 to 48 MHz	–	–	±2	%	With API-called calibration
SID297	$F_{IMOTOL3}$	IMO startup time	–	–	12	µs	–

Internal Low-Speed Oscillator

Table 48. ILO DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID298	I_{ILO2}	ILO operating current at 32 kHz	–	0.3	1.05	µA	–

Table 49. ILO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID299	$T_{STARTILO1}$	ILO startup time	–	–	2	ms	–
SID300	$F_{ILOTRIM1}$	32-kHz trimmed frequency	15	32	50	kHz	–

Table 50. External Clock Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID301	ExtClkFreq	External clock input frequency	0	–	48	MHz	CMOS input level only
SID302	ExtClkDuty	Duty cycle; Measured at $V_{DD/2}$	45	–	55	%	CMOS input level only

Table 51. UDB AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
Data Path performance							
SID303	$F_{MAX-TIMER}$	Max frequency of 16-bit timer in a UDB pair	–	–	48	MHz	–
SID304	$F_{MAX-ADDER}$	Max frequency of 16-bit adder in a UDB pair	–	–	48	MHz	–
SID305	F_{MAX_CRC}	Max frequency of 16-bit CRC/PRS in a UDB pair	–	–	48	MHz	–
PLD Performance in UDB							
SID306	F_{MAX_PLD}	Max frequency of 2-pass PLD function in a UDB pair	–	–	48	MHz	–
Clock to Output Performance							
SID307	$T_{CLK\_OUT\_UDB1}$	Prop. delay for clock in to data out at 25 °C, Typical	–	15	–	ns	–
SID308	$T_{CLK\_OUT\_UDB2}$	Prop. delay for clock in to data out, Worst case	–	25	–	ns	–

Table 52. BLE Subsystem

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
RF Receiver Specification							
SID340	RXS, IDLE	RX sensitivity with idle transmitter	–	–89	–	dBm	–
SID340A		RX sensitivity with idle transmitter excluding Balun loss	–	–91	–	dBm	Guaranteed by design simulation
SID341	RXS, DIRTY	RX sensitivity with dirty transmitter	–	–87	–70	dBm	RF-PHY Specification (RCV-LE/CA/01/C)
SID342	RXS, HIGHGAIN	RX sensitivity in high-gain mode with idle transmitter	–	–91	–	dBm	–
SID343	PRXMAX	Maximum input power	–10	–1	–	dBm	RF-PHY Specification (RCV-LE/CA/06/C)
SID344	CI1	Co-channel interference, Wanted signal at –67 dBm and Interferer at FRX	–	9	21	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID345	CI2	Adjacent channel interference Wanted signal at –67 dBm and Interferer at FRX ±1 MHz	–	3	15	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID346	CI3	Adjacent channel interference Wanted signal at –67 dBm and Interferer at FRX ±2 MHz	–	–29	–	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID347	CI4	Adjacent channel interference Wanted signal at –67 dBm and Interferer at ≥FRX ±3 MHz	–	–39	–	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID348	CI5	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at Image frequency (F_{IMAGE})	–	–20	–	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID349	CI6	Adjacent channel interference Wanted signal at –67 dBm and Interferer at Image frequency (F_{IMAGE} ± 1 MHz)	–	–30	–	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID350	OBB1	Out-of-band blocking, Wanted signal at –67 dBm and Interferer at F = 30–2000 MHz	–30	–27	–	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID351	OBB2	Out-of-band blocking, Wanted signal at –67 dBm and Interferer at F = 2003–2399 MHz	–35	–27	–	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID352	OBB3	Out-of-band blocking, Wanted signal at –67 dBm and Interferer at F = 2484–2997 MHz	–35	–27	–	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID353	OBB4	Out-of-band blocking, Wanted signal a –67 dBm and Interferer at F = 3000–12750 MHz	–30	–27	–	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID354	IMD	Intermodulation performance Wanted signal at –64 dBm and 1-Mbps BLE, third, fourth, and fifth offset channel	–50	–	–	dBm	RF-PHY Specification (RCV-LE/CA/05/C)
SID355	RXSE1	Receiver spurious emission 30 MHz to 1.0 GHz	–	–	–57	dBm	100-kHz measurement bandwidth ETSI EN300 328 V1.8.1

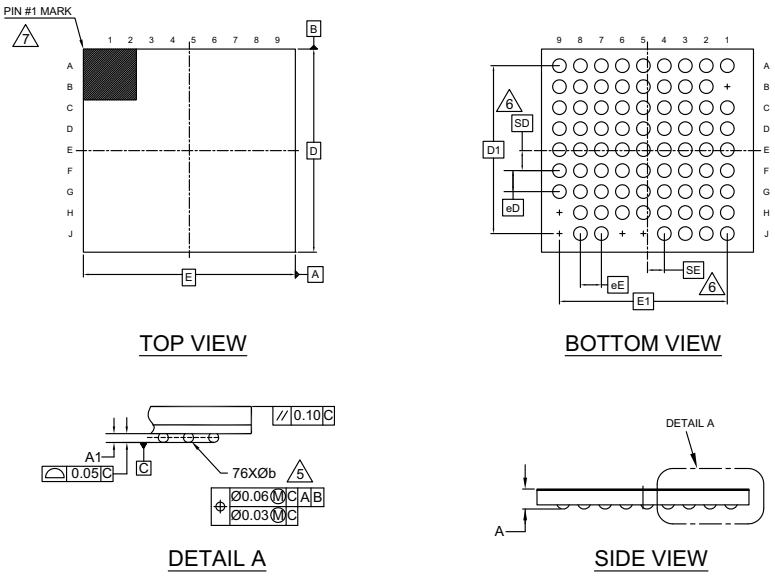
Table 52. BLE Subsystem *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID378	ITX,-6dBm	TX current at –6-dBm setting (PA3)	–	14.5	–	mA	–
SID379	ITX,-12dBm	TX current at –12-dBm setting (PA2)	–	13.2	–	mA	–
SID380	ITX,-18dBm	TX current at –18-dBm setting (PA1)	–	12.5	–	mA	–
SID380A	Iavg_1sec, 0dBm	Average current at 1-second BLE connection interval	–	17.1	–	µA	TXP: 0 dBm; ±20-ppm master and slave clock accuracy.
SID380B	Iavg_4sec, 0dBm	Average current at 4-second BLE connection interval	–	6.1	–	µA	TXP: 0 dBm; ±20-ppm master and slave clock accuracy.
General RF Specifications							
SID381	FREQ	RF operating frequency	2400	–	2482	MHz	–
SID382	CHBW	Channel spacing	–	2	–	MHz	–
SID383	DR	On-air data rate	–	1000	–	kbps	–
SID384	IDLE2TX	BLE.IDLE to BLE. TX transition time	–	120	140	µs	–
SID385	IDLE2RX	BLE.IDLE to BLE. RX transition time	–	75	120	µs	–
RSSI Specifications							
SID386	RSSI, ACC	RSSI accuracy	–	±5	–	dB	–
SID387	RSSI, RES	RSSI resolution	–	1	–	dB	–
SID388	RSSI, PER	RSSI sample period	–	6	–	µs	–

Table 53. ECO Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID389	F_{ECO}	Crystal frequency	–	24	–	MHz	–
SID390	F_{TOL}	Frequency tolerance	–50	–	50	ppm	–
SID391	ESR	Equivalent series resistance	–	–	60	Ω	–
SID392	PD	Drive level	–	–	100	µW	–
SID393	T_{START1}	Startup time (Fast Charge on)	–	–	850	µs	–
SID394	T_{START2}	Startup time (Fast Charge off)	–	–	3	ms	–
SID395	C_L	Load capacitance	–	8	–	pF	–
SID396	C0	Shunt capacitance	–	1.1	–	pF	–
SID397	I_{ECO}	Operating current	–	1400	–	µA	–

Figure 12. 76-Ball WLCSP Package Outline



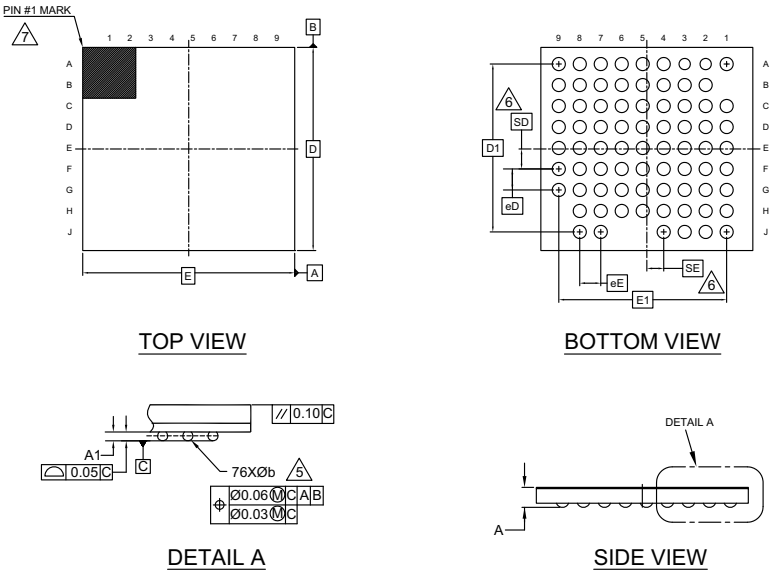
SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	-	-	0.55
A1	0.18	0.21	0.24
D	3.87 BSC		
E	4.04 BSC		
D1	3.20 BSC		
E1	3.20 BSC		
MD	9		
ME	9		
N	76		
Ø b	0.23	0.26	0.29
eD	0.40 BSC		
eE	0.40 BSC		
SD	0.381 BSC		
SE	0.321 BSC		

NOTES:

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. SOLDER BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
3. "e" REPRESENTS THE SOLDER BALL GRID PITCH.
4. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.
   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
   N IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
5. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
6. "SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" OR "SE" = 0.
   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" = eD/2 AND "SE" = eE/2.
7. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.
8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED SOLDER BALLS.
9. JEDEC SPECIFICATION NO. REF : N/A

001-96603 *B

Figure 13. 76-Ball Thin WLCSP Package Outline



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	-	-	0.40
A1	0.072	0.08	0.088
D	3.87 BSC		
E	4.04 BSC		
D1	3.20 BSC		
E1	3.20 BSC		
MD	9		
ME	9		
N	76		
Ø b	0.22	0.25	0.28
eD	0.40 BSC		
eE	0.40 BSC		
SD	0.381		
SE	0.321		

NOTES:

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. SOLDER BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
3. "e" REPRESENTS THE SOLDER BALL GRID PITCH.
4. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION.
   SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION.
   N IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
5. DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
6. "SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW.
   WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" OR "SE" = 0.
   WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" = eD/2 AND "SE" = eE/2.
7. A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.
8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED SOLDER BALLS.

002-10658 **

Acronyms

Table 60. Acronyms Used in this Document

Acronym	Description
abus	analog local bus
ADC	analog-to-digital converter
AG	analog global
AHB	AMBA (advanced microcontroller bus architecture) high-performance bus, an Arm data transfer bus
ALU	arithmetic logic unit
AMUXBUS	analog multiplexer bus
API	application programming interface
APSR	application program status register
Arm®	advanced RISC machine, a CPU architecture
ATM	automatic thump mode
BW	bandwidth
CAN	Controller Area Network, a communications protocol
CMRR	common-mode rejection ratio
CPU	central processing unit
CRC	cyclic redundancy check, an error-checking protocol
DAC	digital-to-analog converter, see also IDAC, VDAC
DFB	digital filter block
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.
DMIPS	Dhrystone million instructions per second
DMA	direct memory access, see also TD
DNL	differential nonlinearity, see also INL
DNU	do not use
DR	port write data registers
DSI	digital system interconnect
DWT	data watchpoint and trace
ECC	error correcting code
ECO	external crystal oscillator
EEPROM	electrically erasable programmable read-only memory
EMI	electromagnetic interference
EMIF	external memory interface
EOC	end of conversion
EOF	end of frame
EPSR	execution program status register
ESD	electrostatic discharge

Table 60. Acronyms Used in this Document *(continued)*

Acronym	Description
ETM	embedded trace macrocell
FIR	finite impulse response, see also IIR
FPB	flash patch and breakpoint
FS	full-speed
GPIO	general-purpose input/output, applies to a PSoC pin
HVI	high-voltage interrupt, see also LVI, LVD
IC	integrated circuit
IDAC	current DAC, see also DAC, VDAC
IDE	integrated development environment
I^2C, or IIC	Inter-Integrated Circuit, a communications protocol
IIR	infinite impulse response, see also FIR
ILO	internal low-speed oscillator, see also IMO
IMO	internal main oscillator, see also ILO
INL	integral nonlinearity, see also DNL
I/O	input/output, see also GPIO, DIO, SIO, USBIO
IPOR	initial power-on reset
IPSR	interrupt program status register
IRQ	interrupt request
ITM	instrumentation trace macrocell
LCD	liquid crystal display
LIN	Local Interconnect Network, a communications protocol.
LR	link register
LUT	lookup table
LVD	low-voltage detect, see also LVI
LVI	low-voltage interrupt, see also HVI
LVTTL	low-voltage transistor-transistor logic
MAC	multiply-accumulate
MCU	microcontroller unit
MISO	master-in slave-out
NC	no connect
NMI	nonmaskable interrupt
NRZ	non-return-to-zero
NVIC	nested vectored interrupt controller
NVL	nonvolatile latch, see also WOL
opamp	operational amplifier
PAL	programmable array logic, see also PLD

Table 60. Acronyms Used in this Document *(continued)*

Acronym	Description
PC	program counter
PCB	printed circuit board
PGA	programmable gain amplifier
PHUB	peripheral hub
PHY	physical layer
PICU	port interrupt control unit
PLA	programmable logic array
PLD	programmable logic device, see also PAL
PLL	phase-locked loop
PMDD	package material declaration data sheet
POR	power-on reset
PRES	precise power-on reset
PRS	pseudo random sequence
PS	port read data register
PSoC®	Programmable System-on-Chip™
PSRR	power supply rejection ratio
PWM	pulse-width modulator
RAM	random-access memory
RISC	reduced-instruction-set computing
RMS	root-mean-square
RTC	real-time clock
RTL	register transfer language
RTR	remote transmission request
RX	receive
SAR	successive approximation register
SC/CT	switched capacitor/continuous time
SCL	I^2C serial clock
SDA	I^2C serial data
S/H	sample and hold
SINAD	signal to noise and distortion ratio
SIO	special input/output, GPIO with advanced features. See GPIO.
SOC	start of conversion
SOF	start of frame
SPI	Serial Peripheral Interface, a communications protocol
SR	slew rate
SRAM	static random access memory
SRES	software reset
SWD	serial wire debug, a test protocol

Table 60. Acronyms Used in this Document *(continued)*

Acronym	Description
SWV	single-wire viewer
TD	transaction descriptor, see also DMA
THD	total harmonic distortion
TIA	transimpedance amplifier
TRM	technical reference manual
TTL	transistor-transistor logic
TX	transmit
UART	Universal Asynchronous Transmitter Receiver, a communications protocol
UDB	universal digital block
USB	Universal Serial Bus
USBIO	USB input/output, PSoC pins used to connect to a USB port
VDAC	voltage DAC, see also DAC, IDAC
WDT	watchdog timer
WOL	write once latch, see also NVL
WRES	watchdog timer reset
XRES	external reset I/O pin
XTAL	crystal

Revision History

Description Title: PSoC® 4: 4200_BLE Family Datasheet Programmable System-on-Chip (PSoC®) Document Number: 002-23053				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
**	6078076	PMAD/ WKA	02/22/2018	New datasheet